



Description

The IRFR120NPBF uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

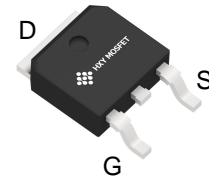
$V_{DS} = 100V, I_D = 15A$

$R_{DS(ON)} < 112m\Omega @ V_{GS} = 10V$

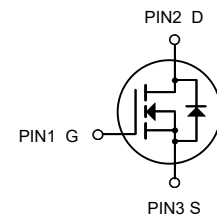
Application

Power switch

DC/DC converters



TO-252-2L
(DPAK)



N-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRFR120NPBF	TO-252-2L(DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.7	A
I_{DM}	Pulsed Drain Current ²	24	A
EAS	Single Pulse Avalanche Energy ³	6.1	mJ
I_{AS}	Avalanche Current	11	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ³	34.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	3.6	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25 °C, I _D =1mA	---	0.098	---	V/°C
R _{DS(on)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =10A	---	100	112	mΩ
		V _{GS} =4.5V, I _D =8A	---	117	130	mΩ
V _{GS(th)}	Gate Threshold Voltage		1.0	---	2.5	V
		V _{GS} =V _{DS} , I _D =250uA				
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.57	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25 °C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55 °C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =10A	---	13	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2	---	Ω
Q _g	Total Gate Charge (10V)		---	26.2	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =80V, V _{GS} =10V, I _D =10A	---	4.6	---	
Q _{gd}	Gate-Drain Charge		---	5.1	---	
T _{d(on)}	Turn-On Delay Time		---	4.2	---	ns
T _r	Rise Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3	---	8.2	---	
T _{d(off)}	Turn-Off Delay Time	I _D =10A	---	35.6	---	
T _f	Fall Time		---	9.6	---	
C _{iss}	Input Capacitance		---	1535	---	pF
C _{oss}	Output Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	60	---	
C _{rss}	Reverse Transfer Capacitance		---	37	---	
I _S	Continuous Source Current ^{1,5}		---	---	12	A
I _{SM}	Pulsed Source Current ^{2,5}	V _G =V _D =0V, Force Current	---	---	24	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25 °C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =10A, di/dt=100A/μs	---	37	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25 °C	---	27.3	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=11A
- 4.The power dissipation is limited by 150 °C junction temperature
- 5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

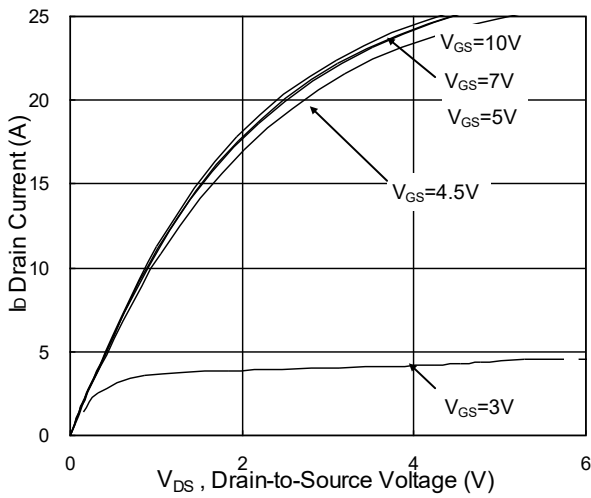


Fig.1 Typical Output Characteristics

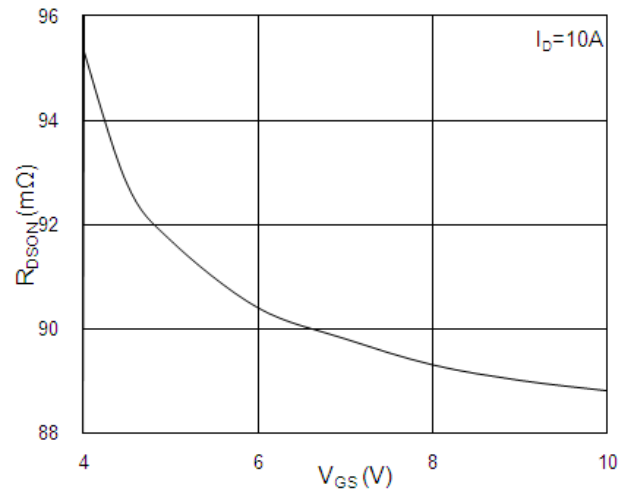


Fig.2 On-Resistance vs. Gate-Source

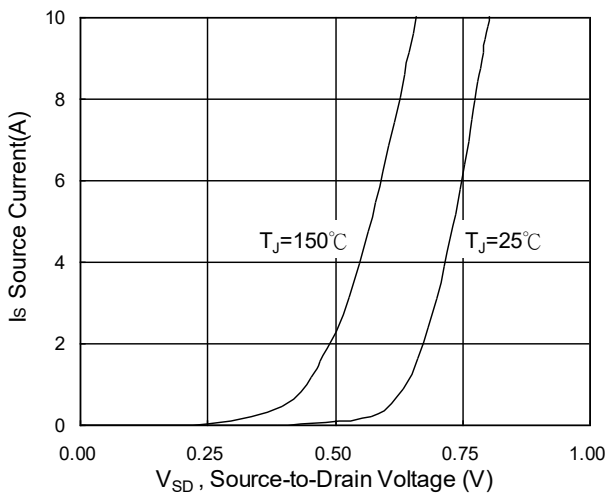


Fig.3 Forward Characteristics Of Reverse

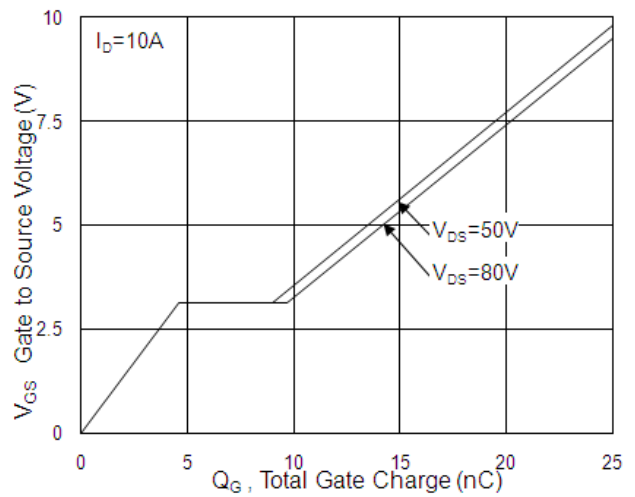


Fig.4 Gate-Charge Characteristics

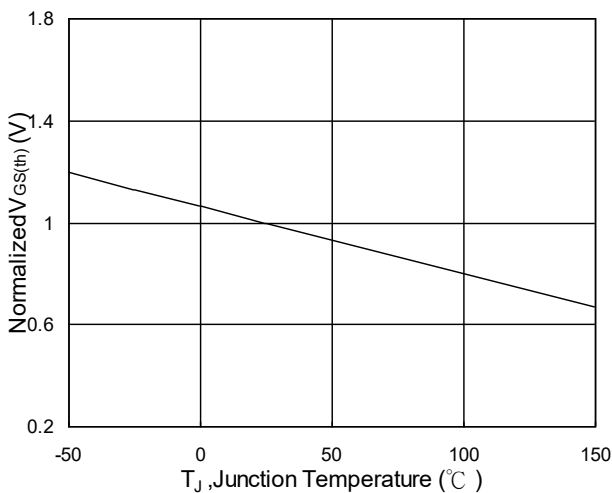


Fig.5 Normalized V_{GS(th)} vs. T_J

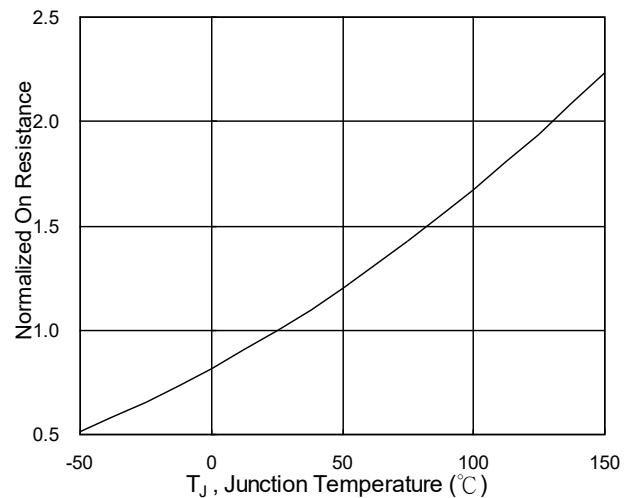


Fig.6 Normalized R_{DS(on)} vs. T_J

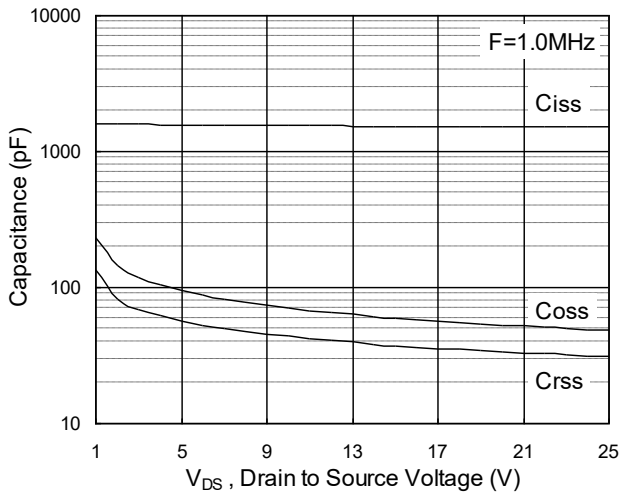


Fig.7 Capacitance

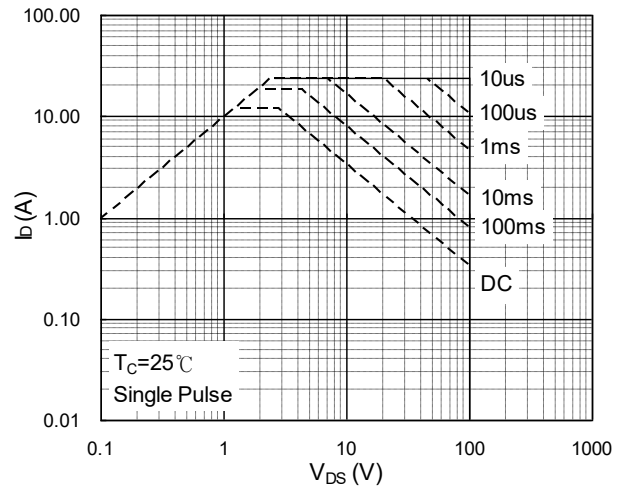


Fig.8 Safe Operating Area

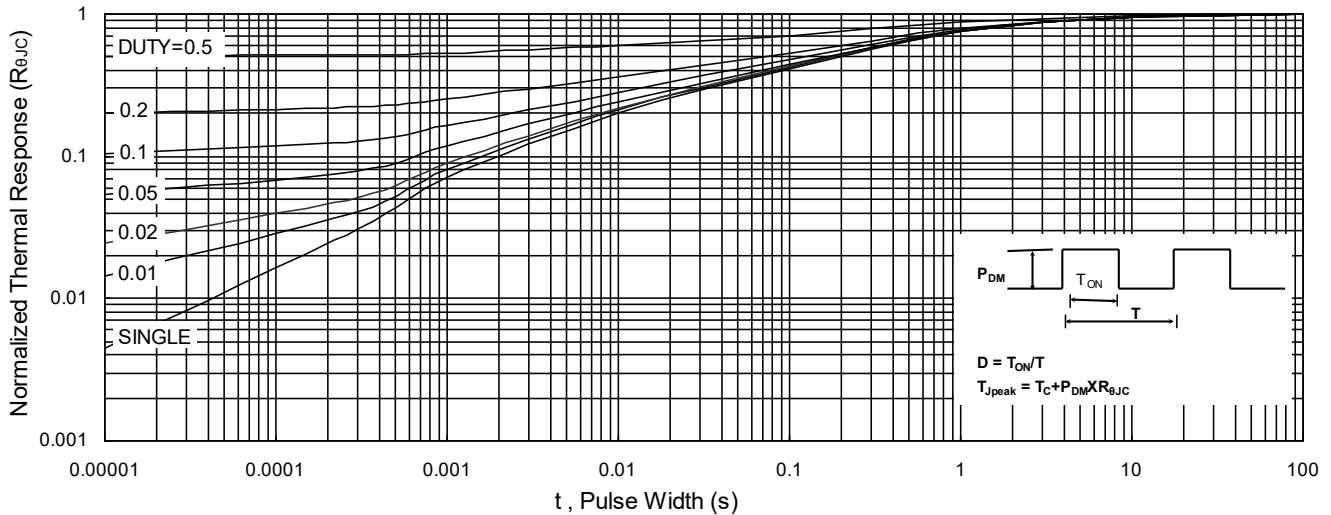


Fig.9 Normalized Maximum Transient Thermal Impedance

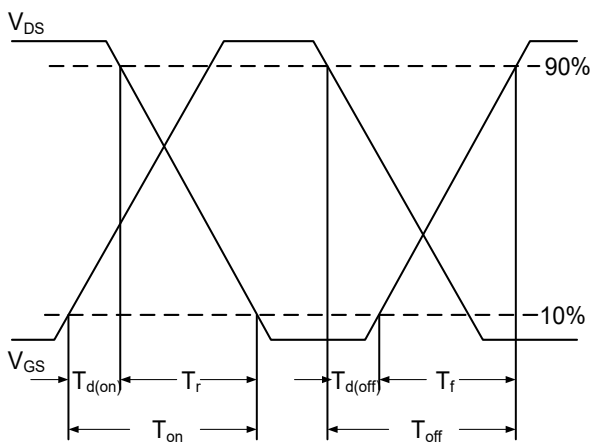


Fig.10 Switching Time Waveform

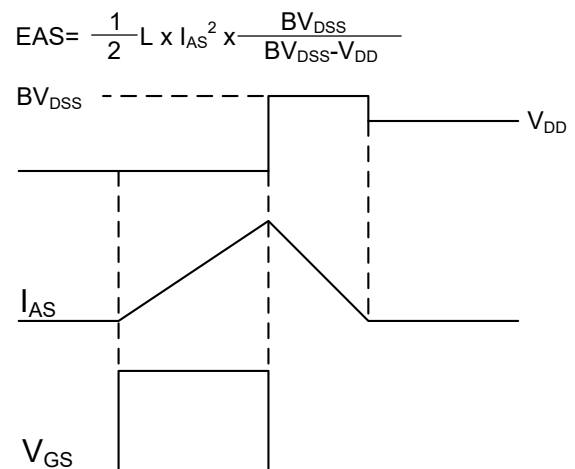


Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



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